

# SD101AW...SD101CW Surface Mount Schottky Barrier Diodes

### **Features**

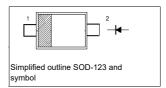
- Low forward voltage
- Low reverse capacitance

#### **INFORMATION**

Type No.	Marking		
SD101AW	S1		
SD101BW	<b>S2</b>		
SD101CW	<b>S</b> 3		

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



# Absolute Maximum Ratings (T $_a$ = 25 $_{\circ}$ C)

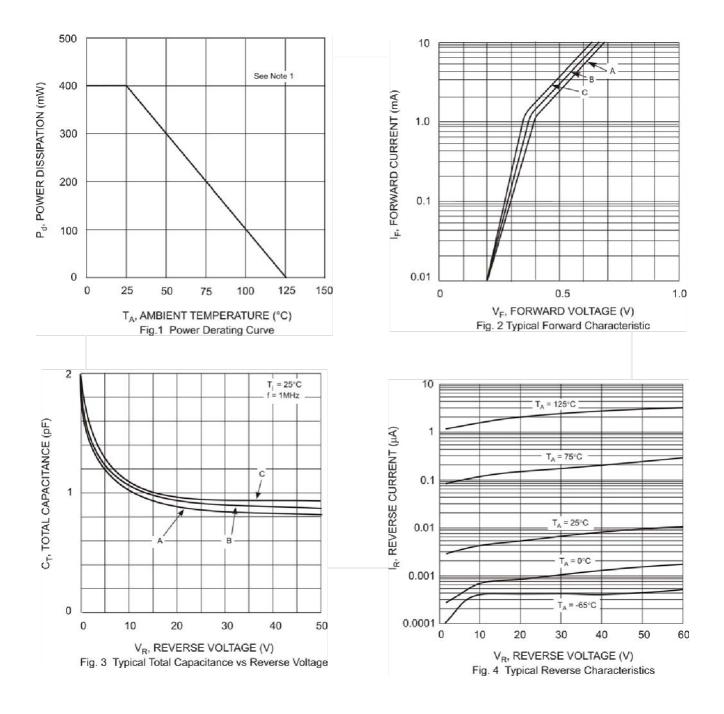
Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage	SD101AW SD101BW	VRRM	60 50	V
Reverse Voltage	SD101CW SD101AW SD101BW SD101CW	V <sub>R</sub>	40 60 50 40	V
Forward Continuous Current	02.0.0.	<b>I</b> FM	15	mA
Power Dissipation	ower Dissipation		400	mW
Non-Repetitive Peak Forward Surge Current	at t = 1 s at t = 10 µs	İFSM	50 2	mA A
Operating and Storage Temperature Range		Tj, Tstg	- 65 to + 125	°C

# Characteristics at T<sub>a</sub> = 25 °C

Parameter		Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage					
at I <sub>R</sub> = 10 μA	SD101AW		60	-	.,
	SD101BW	V (BR)R	50	-	V
	SD101CW		40	-	
Forward Voltage					
at I <sub>F</sub> = 1 mA	SD101AW		-	0.41	
	SD101BW		-	0.4	
	SD101CW	$V_{F}$	-	0.39	V
at I <sub>F</sub> = 15 mA	SD101AW		-	1	
	SD101BW		-	0.95	
	SD101CW		-	0.9	
Reverse Current					
at V <sub>R</sub> = 50 V	SD101AW		-	200	
at V <sub>R</sub> = 40 V	SD101BW	I <sub>R</sub>	-	200	nA
at V <sub>R</sub> = 30 V	SD101CW		-	200	
Total Capacitance					
at $V_R = 0 V$ , $f = 1 MHz$	SD101AW		-	2	
	SD101BW	C <sub>T</sub>	-	2.1	pF
	SD101CW			2.2	
Reverse Recovery Time		4		1	no
at $I_F = I_R = 5 \text{ mA}$ , $I_{rr} = 0.1 \text{X}$ $I_{R_r}$ $R_L = 100 \Omega$		t <sub>rr</sub>	-	1	ns



## TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified





### **PACKAGE OUTLINE**

### Plastic surface mounted package; 2 leads

**SOD-123** 

